



#### Product Summary

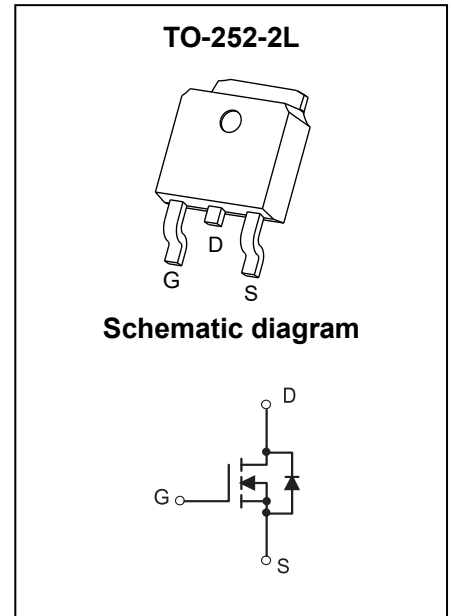
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
150V	240mΩ@10V	8.6A

#### Feature

- Trench Technology Power MOSFET
- Low  $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

#### Application

- Power Switching Application
- Hard Switched and High Frequency Circuits



#### Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPM24DN15NTF	TO-252-2L	M24DN15N	Reel & Tape	330mm	16mm	2500pcs

#### ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain - Source Voltage	$V_{DS}$	150	V	
Gate - Source Voltage	$V_{GS}$	±20	V	
Continuous Drain Current <sup>1</sup>	$T_C = 25^\circ\text{C}$	$I_D$	8.6	A
	$T_C = 100^\circ\text{C}$	$I_D$	5.4	A
Pulsed Drain Current <sup>2</sup>	$I_{DM}$	34	A	
Power Dissipation <sup>5</sup>	$T_C = 25^\circ\text{C}$	$P_D$	39	W
Thermal Resistance from Junction to Ambient <sup>5</sup>	$R_{\theta JA}$	65	$^\circ\text{C}/\text{W}$	
Thermal Resistance from Junction to Case	$R_{\theta JC}$	3.2	$^\circ\text{C}/\text{W}$	
Junction Temperature	$T_J$	150	$^\circ\text{C}$	
Storage Temperature	$T_{STG}$	-55~ +150	$^\circ\text{C}$	

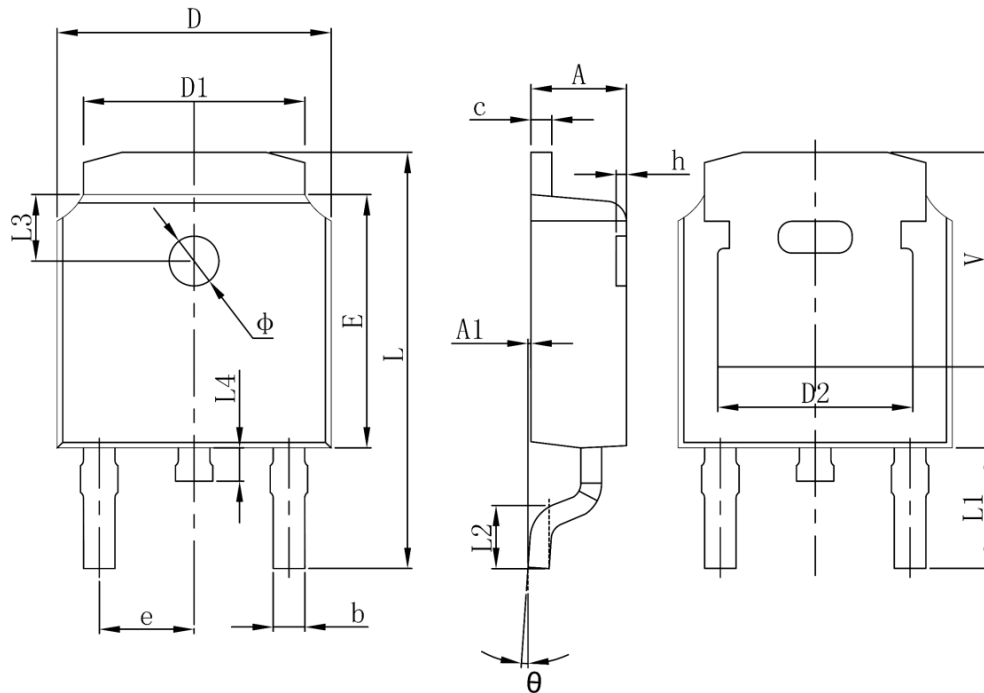
## MOSFET ELECTRICAL CHARACTERISTICS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Off Characteristics</b>						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	150			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 150V, V_{GS} = 0V$			1	$\mu A$
Gate - Body Leakage Current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$			$\pm 150$	nA
<b>On Characteristics<sup>3</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.5	2	2.5	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 5A$		240	300	m $\Omega$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 75V, V_{GS} = 0V, f = 1MHz$		450		pF
Output Capacitance	$C_{oss}$			13		
Reverse Transfer Capacitance	$C_{rss}$			10		
Gate Resistance	$R_g$	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		1.4		$\Omega$
<b>Switching Characteristics</b>						
Total Gate Charge	$Q_g$	$V_{DS} = 75V, V_{GS} = 10V, I_D = 1.5A$		17		nC
Gate-source Charge	$Q_{gs}$			2.6		
Gate-drain Charge	$Q_{gd}$			5.8		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 75V, V_{GS} = 10V, R_G = 6\Omega, I_D = 1A$		9.4		ns
Turn-on Rise Time	$t_r$			11		
Turn-off Delay Time	$t_{d(off)}$			24		
Turn-off Fall Time	$t_f$			18		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage <sup>3</sup>	$V_{SD}$	$V_{GS} = 0V, I_S = 5A$			1.2	V

### Notes :

- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width  $\leq 10\mu s$ , duty cycle  $\leq 1\%$ .
- 3.Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
- 4.The power dissipation  $P_D$  is limited by  $T_{J(MAX)} = 150^\circ\text{C}$ .And device mounted on a large heatsink
- 5.Device mounted on  $1\text{in}^2$  FR-4 board with 2oz. Copper, in a still air environment with  $T_A = 25^\circ\text{C}$ .

## TO-252-2L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.635	0.860	0.025	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830REF		0.190REF	
E	6.000	6.300	0.236	0.248
e	2.186	2.386	0.086	0.094
L	9.712	10.312	0.382	0.406
L1	2.900REF		0.114REF	
L2	1.400	1.700	0.055	0.067
L3	1.600REF		0.063REF	
L4	0.600	1.000	0.024	0.039
$\phi$	1.100	1.300	0.043	0.051
$\theta$	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.250REF		0.207REF	